

**In the Claims:**

1. (withdrawn)
  2. (withdrawn)
  3. (withdrawn)
  4. (withdrawn)
  5. (withdrawn)
  6. (withdrawn)
  7. (cancelled)
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8. (cancelled)
  9. (cancelled)
  10. (cancelled)
  11. (cancelled)
  12. (currently amended) A method of endpoint detection in plasma etching of a target layer of material, comprising the actions of:  
measuring voltage across a plasma system by measuring a voltage ~~difference~~ across an element that is external to said plasma system;  
detecting a change of the voltage prior to the completion of the etching of the target layer of material; and  
stopping etch when said voltage ~~decreases~~ change exceeds a predetermined amount within a predetermined time.
  13. (original) The method of Claim 12, wherein said element is a resistor.
  14. (previously amended) The method of Claim 12, wherein said predetermined amount is a voltage change of not less than 5% from a reference voltage and said predetermined time is not less than 3 seconds.
  15. (cancelled)
  16. (cancelled)
  17. (cancelled)
  18. (cancelled)
  19. (new) The method of Claim 12, wherein the element is part of an impedance matching network.